SHENZHEN YIXINWEI TECHNOLOGY CO.,LTD

AOD422

20V N-Channel MOSFET

General Description

The AOD422 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected.

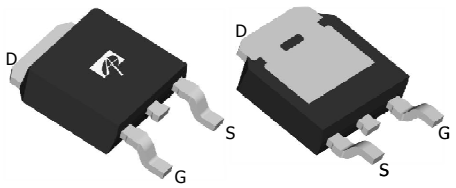
Product Summary

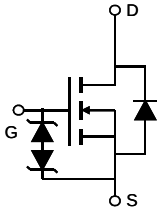
V_{DS}	20V
I_D (at V_{GS}=4.5V)	20A
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 25mΩ
$R_{DS(ON)}$ (at V_{GS} =2.5V)	< 28mΩ
$R_{DS(ON)}$ (at V_{GS} =1.8V)	< 34mΩ

ESD protected
100% UIS Tested

Green Product

TO252 DPAK





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current [G]	T_C=25℃	I_D	20	A
	T_C=100℃		16	
Pulsed Drain Current [C]		I_{DM}	90	
Continuous Drain Current	T_A=25℃	I_{DSM}	8	A
	T_A=70℃		6.5	
Avalanche Current [C]		I_{AS}, I_{AR}	15	A
Avalanche energy L=0.1mH [C]		E_{AS}, E_{AR}	11	mJ
Power Dissipation [B]	T_C=25℃	P_D	37	W
	T_C=100℃		18	
Power Dissipation [A]	T_A=25℃	P_{DSM}	2.5	W
	T_A=70℃		1.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	16.7	25	℃/W
Maximum Junction-to-Ambient [A D]	Steady-State		40	50	℃/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	3	4	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=20V, V_{GS}=0V			1	μA
		T_J=55℃			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±4.5V			±1	uA
		V_{DS}=0V, V_{GS}= ±8V			±10	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA	0.4	0.7	1.1	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	45			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=10A		16	25	mΩ
		T_J=125℃		22	31	
		V_{GS}=2.5V, I_D=8A		18	28	mΩ
		V_{GS}=1.8V, I_D=5A		21	34	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=10A		55		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.62	1	V
I_S	Maximum Body-Diode Continuous Current				20	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz	1035	1295	1650	pF
C_{oss}	Output Capacitance		110	160	210	pF
C_{rss}	Reverse Transfer Capacitance		50	87	125	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.9	1.8	2.7	KΩ
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=10A		10		nC
Q_{gs}	Gate Source Charge			4.2		nC
Q_{gd}	Gate Drain Charge			2.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=10V, R_L=1Ω, R_{GEN}=3Ω		280		ns
t_r	Turn-On Rise Time			328		ns
$t_{D(off)}$	Turn-Off DelayTime			3.76		us
t_f	Turn-Off Fall Time			2.24		us
t_{rr}	Body Diode Reverse Recovery Time	I_F=10A, dI/dt=500A/μs, V_{GS}=-9V		25		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=10A, dI/dt=500A/μs, V_{GS}=-9V		75		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.
B. The power dissipation P_D is based on $T_{J(MAX)}$=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=175° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

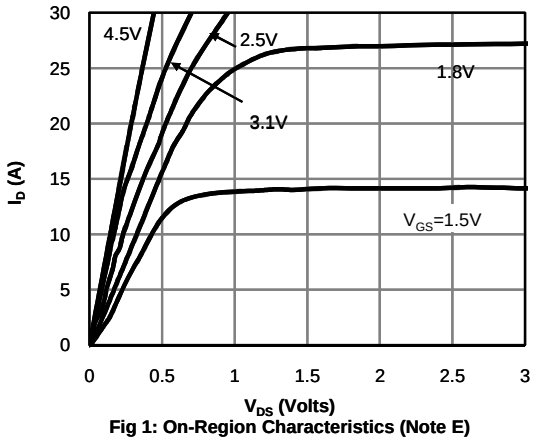


Fig 1: On-Region Characteristics (Note E)

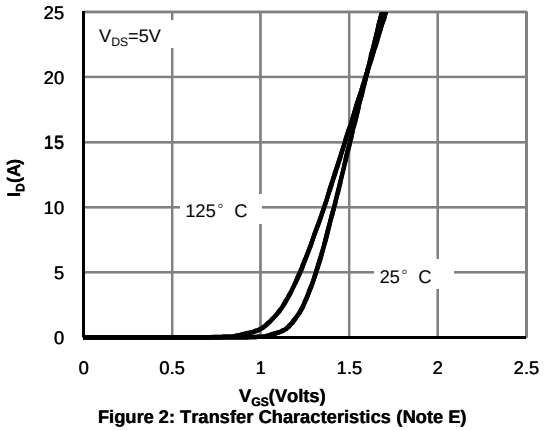


Figure 2: Transfer Characteristics (Note E)

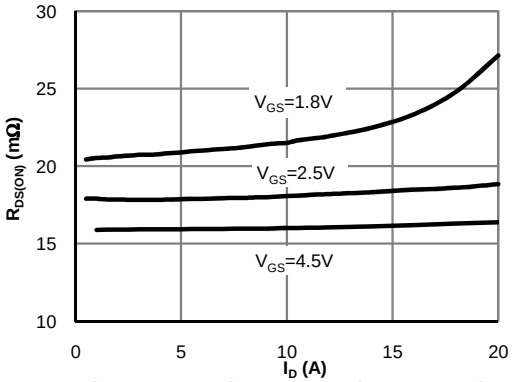


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

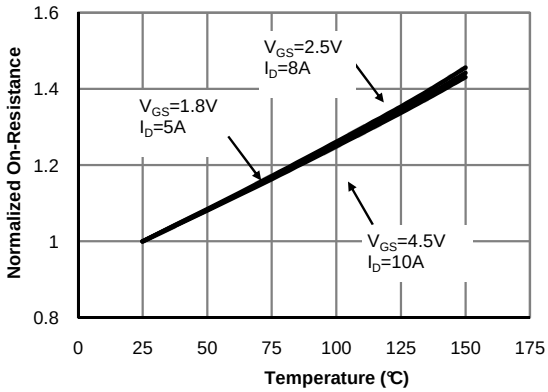


Figure 4: On-Resistance vs. Junction Temperature (Note E)

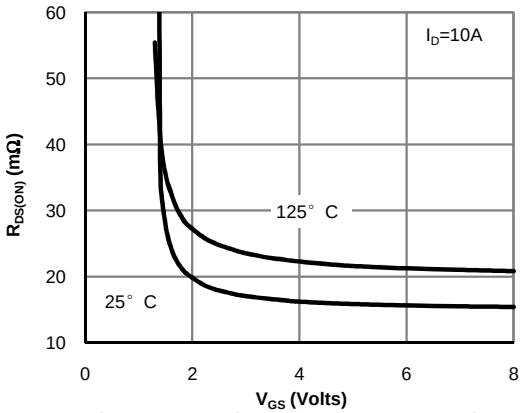


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

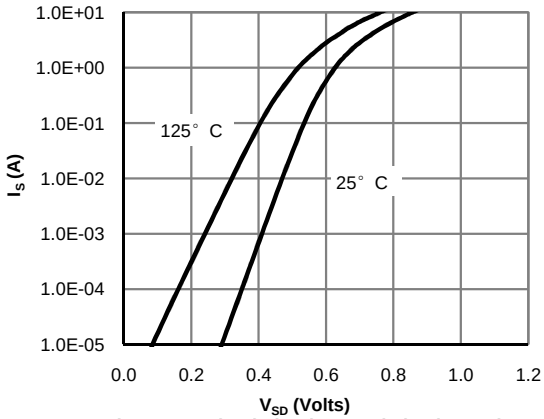


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

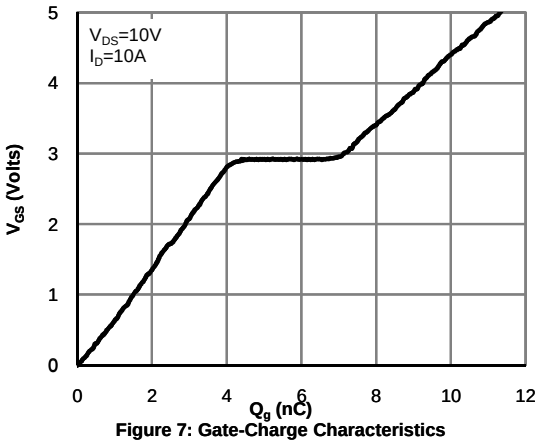


Figure 7: Gate-Charge Characteristics

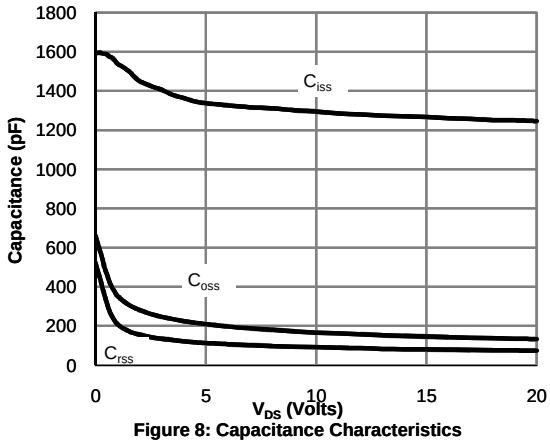


Figure 8: Capacitance Characteristics

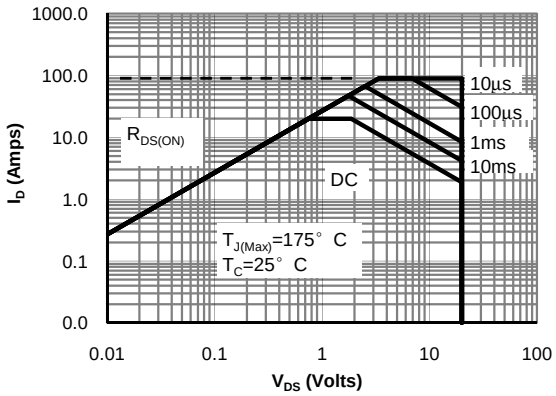


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

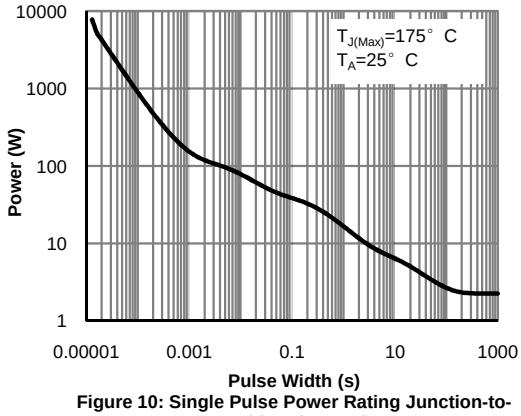


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note H)

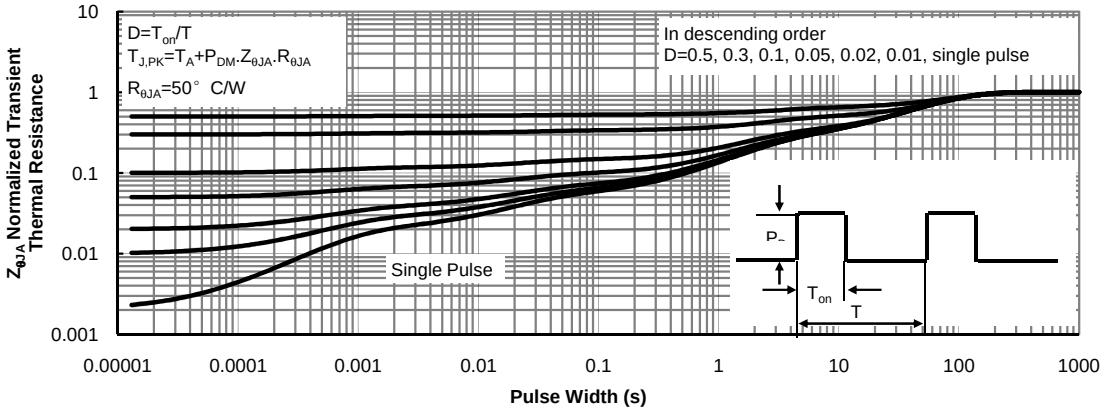
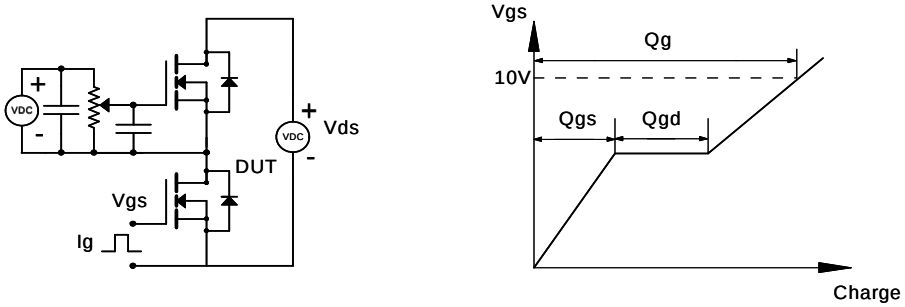
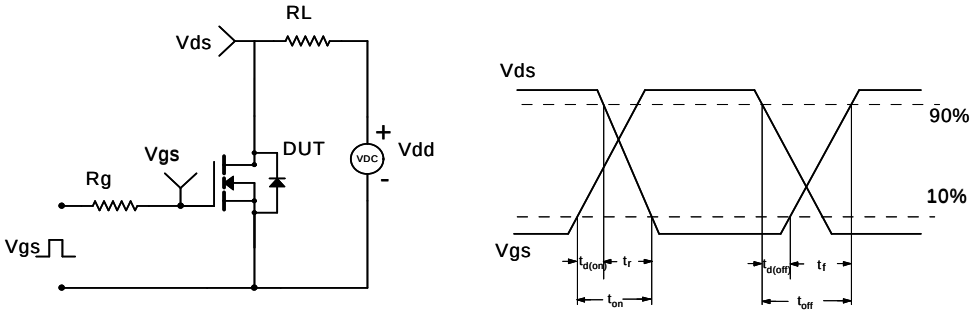


Figure 11: Normalized Maximum Transient Thermal Impedance (Note H)

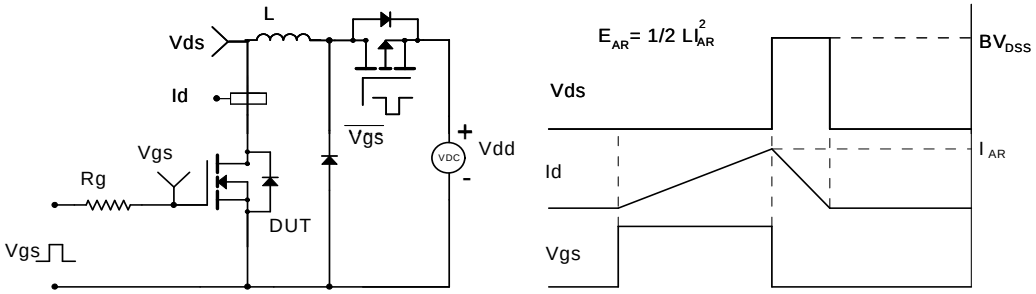
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms